

DOSEMI

IGBT

DG75X12T2

1200V/75A IGBT with Diode

General Description

DOSEMI IGBT Power Discrete provides ultra low conduction loss as well as low switching loss. They are designed for the applications such as general inverters and UPS.

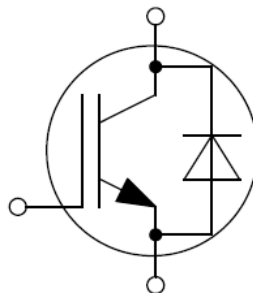
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Low switching loss
- Maximum junction temperature 175°C
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Lead free package

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=137^{\circ}\text{C}$	150 75	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	300	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	1415	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	300	A

Discrete

Symbol	Description	Values	Unit
T_{jop}	Operating Junction Temperature	-40 to +175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$
T_S	Soldering Temperature, 1.6mm from case for 10s	260	$^{\circ}\text{C}$

IGBT Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.75	2.20	V
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		2.00		
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		2.05		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.72\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.6	6.2	6.8	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			2.0		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		7.04		nF
C_{res}	Reverse Transfer Capacitance			0.20		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.53		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		137		ns
t_r	Rise Time			26		ns
$t_{d(off)}$	Turn-Off Delay Time			333		ns
t_f	Fall Time			78		ns
E_{on}	Turn-On Switching Loss			2.91		mJ
E_{off}	Turn-Off Switching Loss			4.11		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		146		ns
t_r	Rise Time			34		ns
$t_{d(off)}$	Turn-Off Delay Time			421		ns
t_f	Fall Time			147		ns
E_{on}	Turn-On Switching Loss			6.25		mJ
E_{off}	Turn-Off Switching Loss			6.26		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		146		ns
t_r	Rise Time			34		ns
$t_{d(off)}$	Turn-Off Delay Time			441		ns
t_f	Fall Time			166		ns
E_{on}	Turn-On Switching Loss			7.28		mJ
E_{off}	Turn-Off Switching Loss			7.05		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		300		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		2.15	2.60	V
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		2.15		
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		2.15		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=2300\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		6.0		μC
I_{RM}	Peak Reverse Recovery Current			74		A
E_{rec}	Reverse Recovery Energy			2.67		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=2300\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		9.4		μC
I_{RM}	Peak Reverse Recovery Current			70		A
E_{rec}	Reverse Recovery Energy			3.61		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=2300\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		9.6		μC
I_{RM}	Peak Reverse Recovery Current			63		A
E_{rec}	Reverse Recovery Energy			3.74		mJ

Discrete Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT)			0.106	K/W
	Junction-to-Case (per Diode)			0.174	
R_{thJA}	Junction-to-Ambient		40		K/W

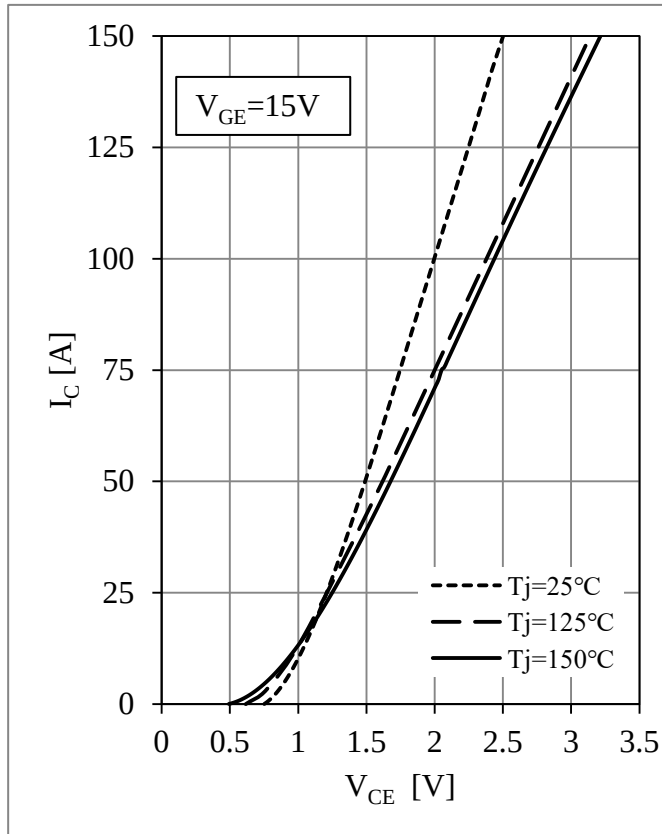


Fig 1. IGBT-inverter Output Characteristics

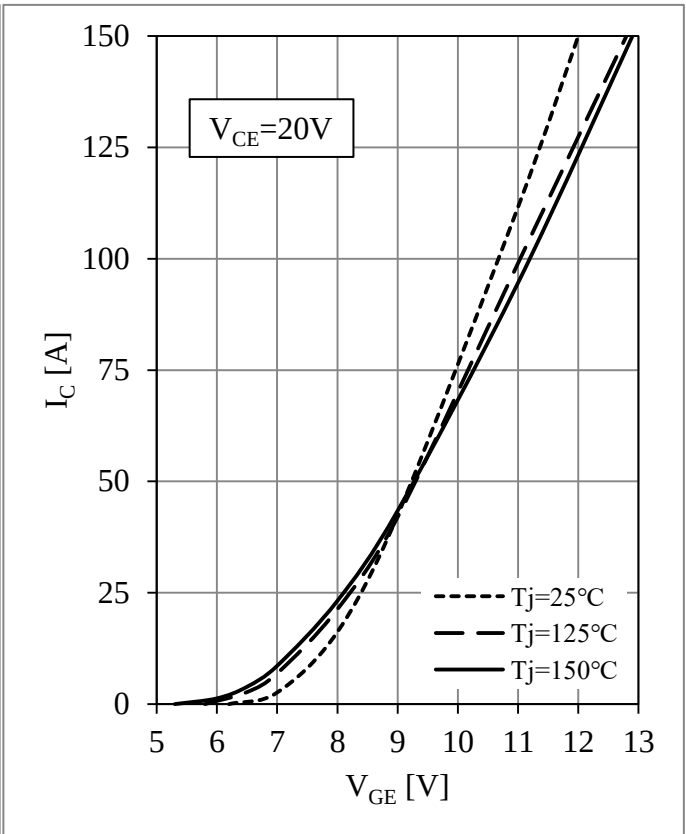
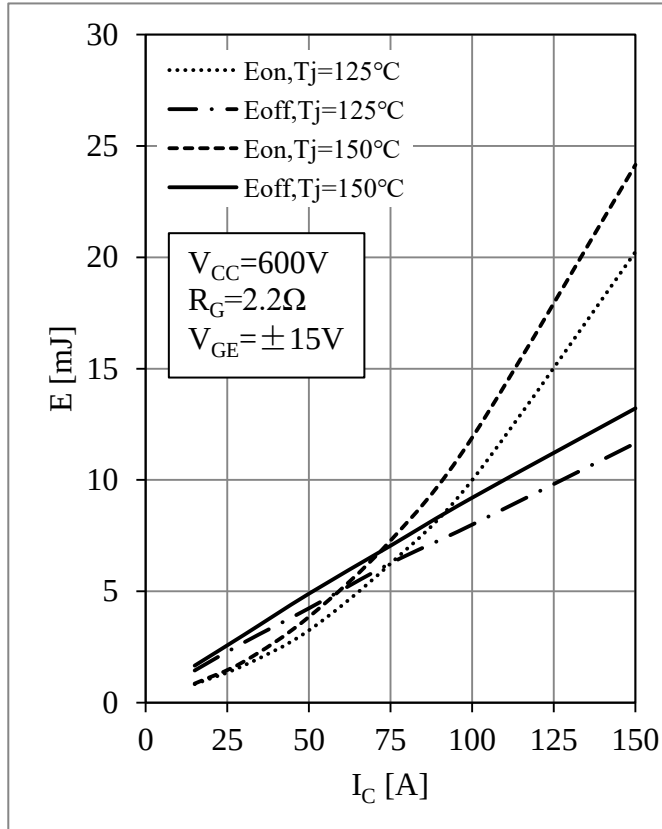
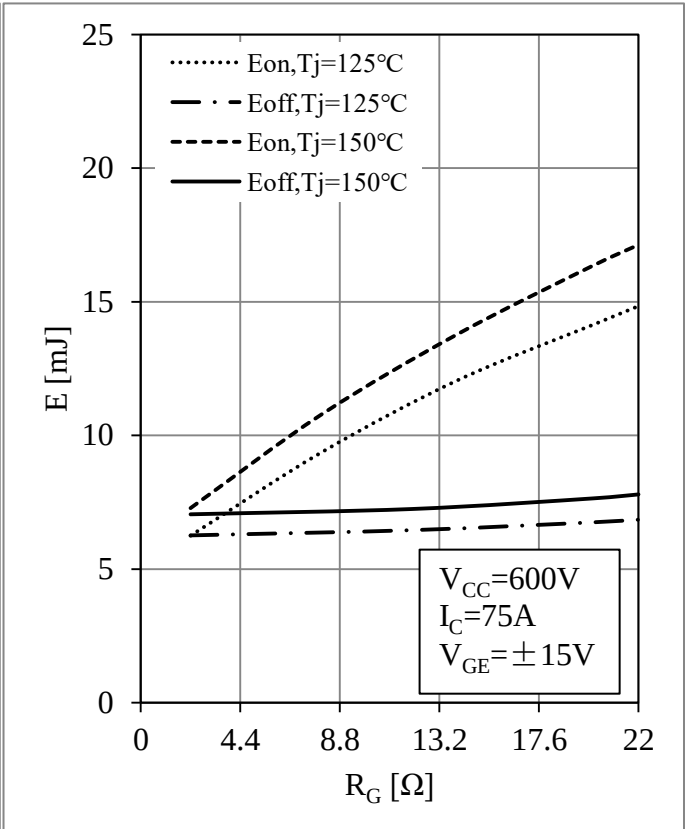


Fig 2. IGBT-inverter Transfer Characteristics

Fig 3. IGBT-inverter Switching Loss vs. I_C Fig 4. IGBT-inverter Switching Loss vs. R_G

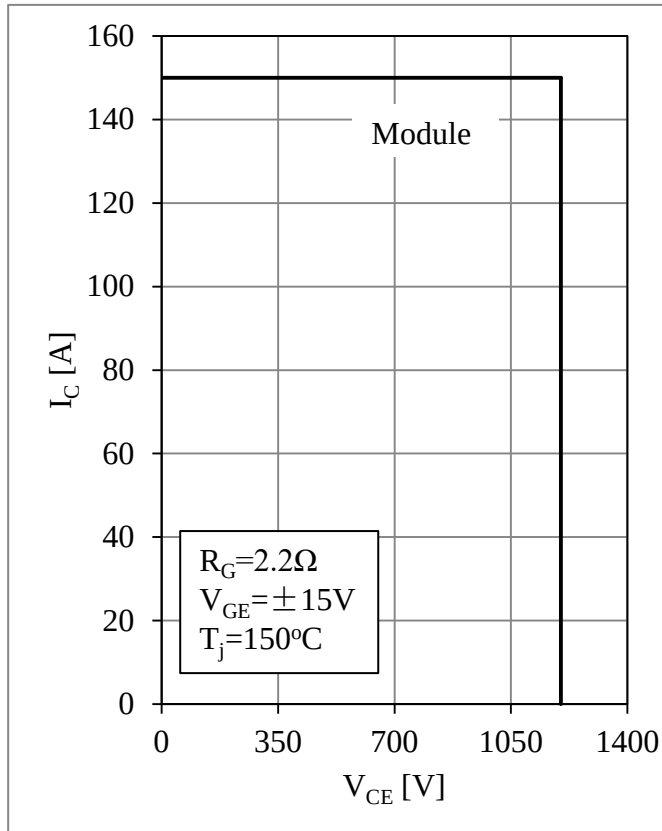


Fig 5. IGBT-inverter RBSOA

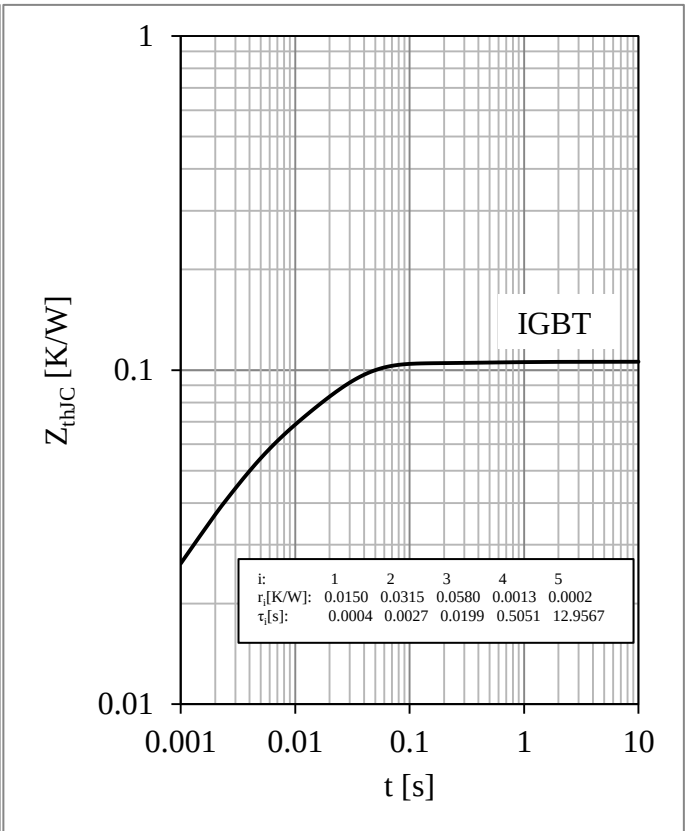


Fig 6. IGBT-inverter Transient Thermal Impedance

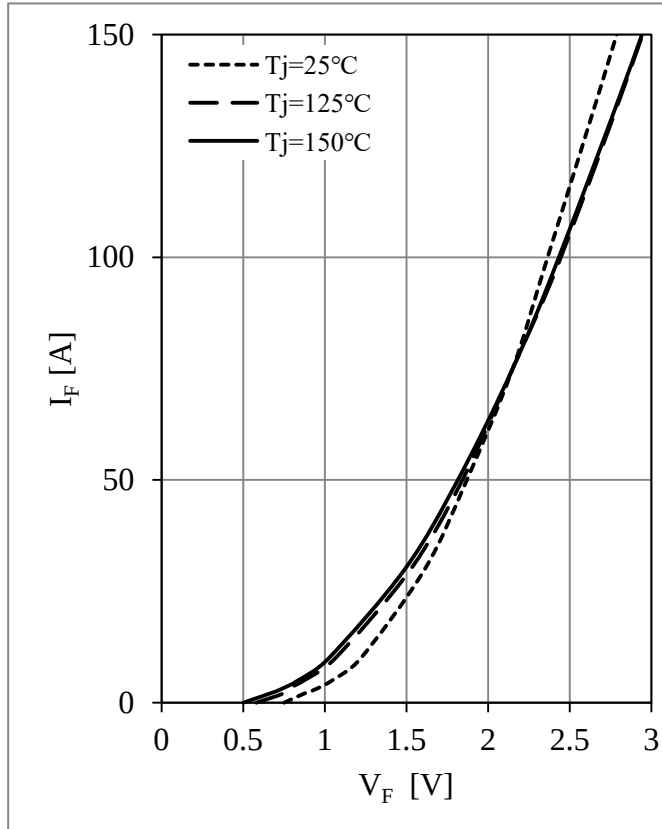
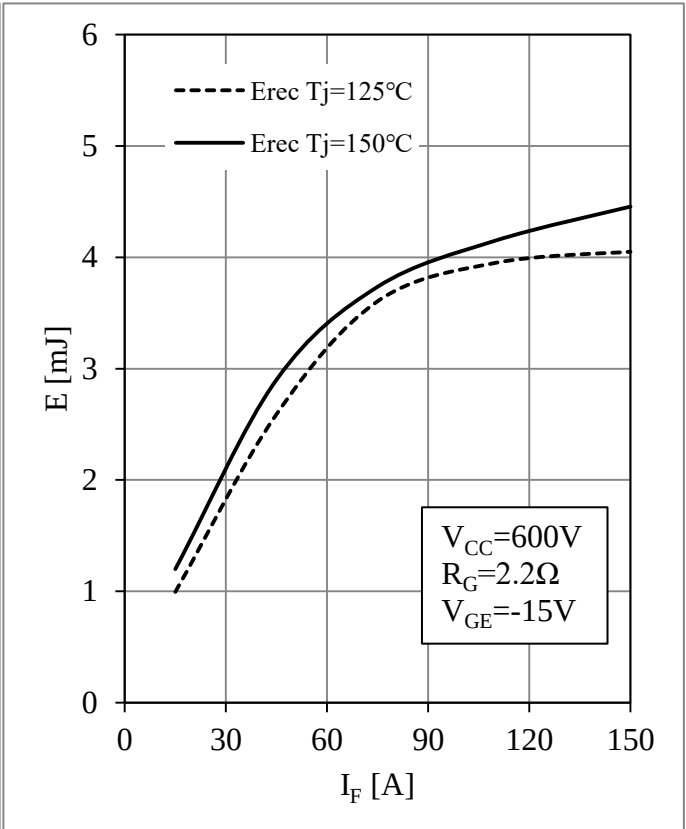


Fig 7. Diode-inverter Forward Characteristics

Fig 8. Diode-inverter Switching Loss vs. I_F

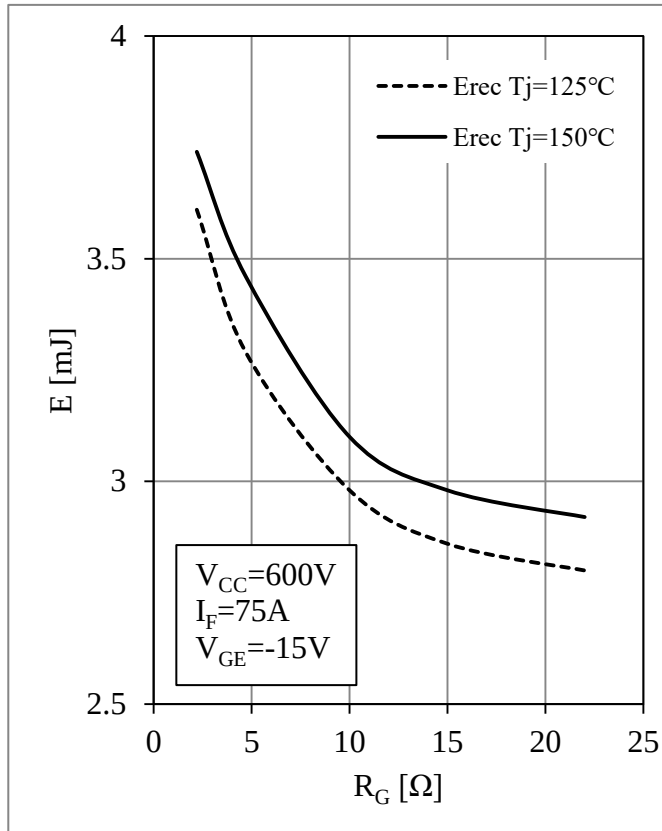
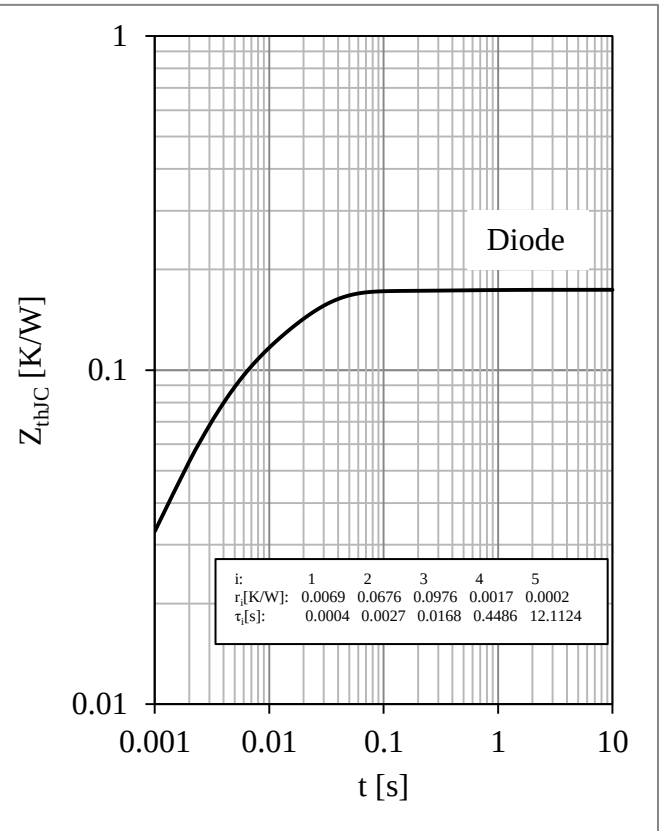
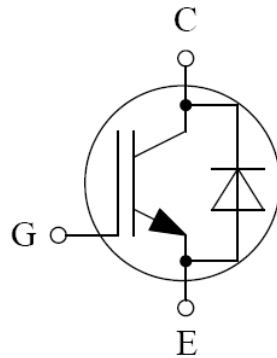
Fig 9. Diode-inverter Switching Loss vs. R_G 

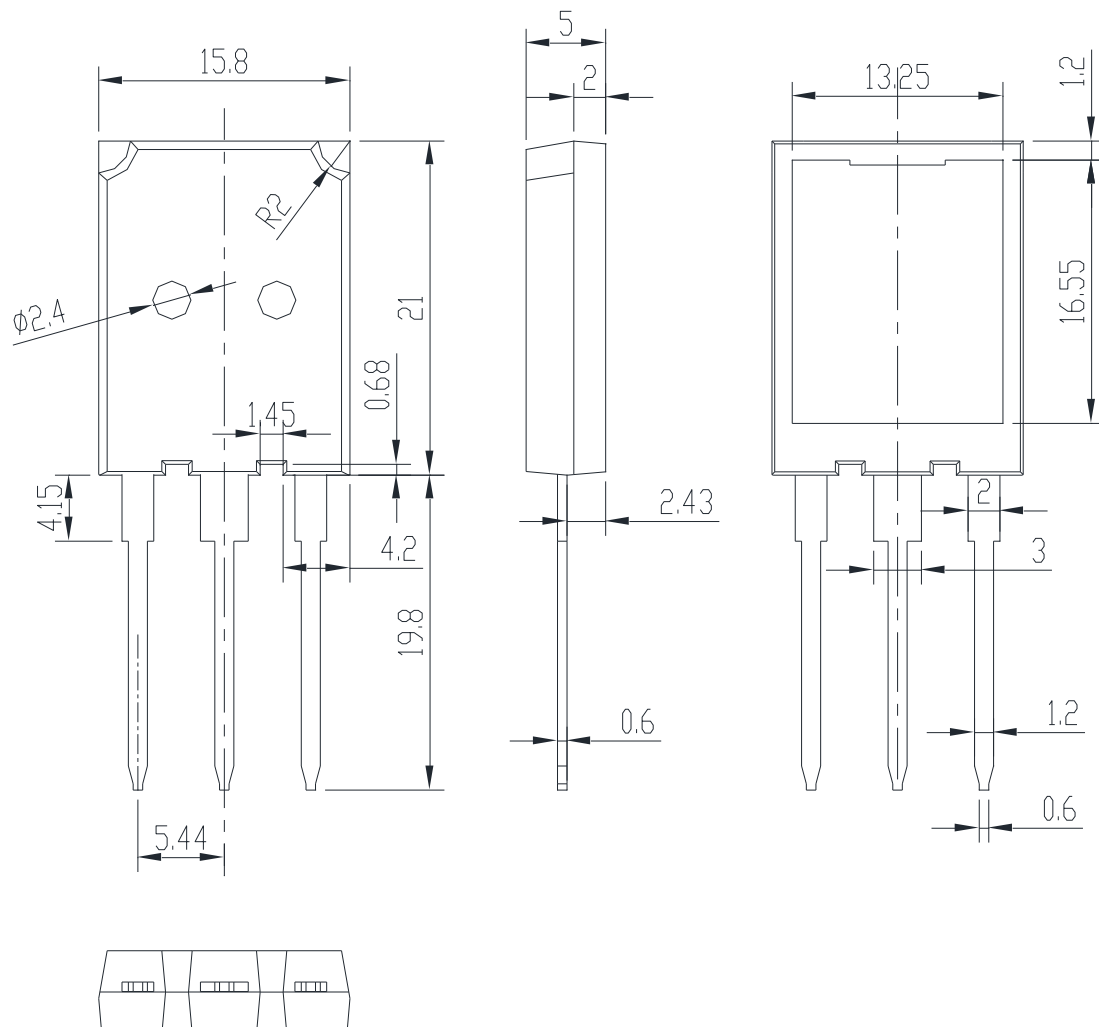
Fig 10. Diode-inverter Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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